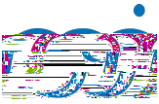


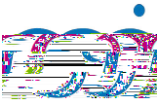
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Maximum Ratings

Parameter	Symbol	Value	Unit
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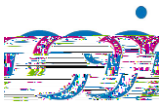




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Electrical Characteristics of the Diode $T_j = 25$ unless otherwise specified

Parameter	Symbol
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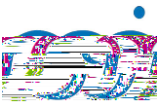
Electrical Characteristics of the DIODE

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T_j= 25						
Reverse Recovery Current	I _{rr}	I _F =75A, V _R =600V, di/dt= -500	-	9	-	A
Diode reverse recovery time	trr		-	268	-	ns
Reverse Recovery Charge	Q _{rr}		-	3.42	-	uC
Reverse Recovery Energy	E _{rec}		-	1.52	-	mJ
Dynamic , at T_j= 125						
Reverse Recovery Current	I _{rr}	I _F =75A, V _R =600V, di/dt= -500	-	12	-	A
Diode reverse recovery time	trr		-	337	-	ns
Reverse Recovery Charge	Q _{rr}		-	6.58	-	uC
Reverse Recovery Energy	E _{rec}		-	3.18	-	mJ
Dynamic , at T_j= 150						
Reverse Recovery Current	I _{rr}	I _F =75A, V _R =600V, di/dt= -500	-	14	-	A
Diode reverse recovery time	trr		-	375	-	ns
Reverse Recovery Charge	Q _{rr}		-	9.45	-	uC
Reverse Recovery Energy	E _{rec}		-	3.73	-	mJ

Thermal Resistance

Parameter	Symbol	Max. Value	Unit
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IGBT Thermal Resistance, Junction - Case



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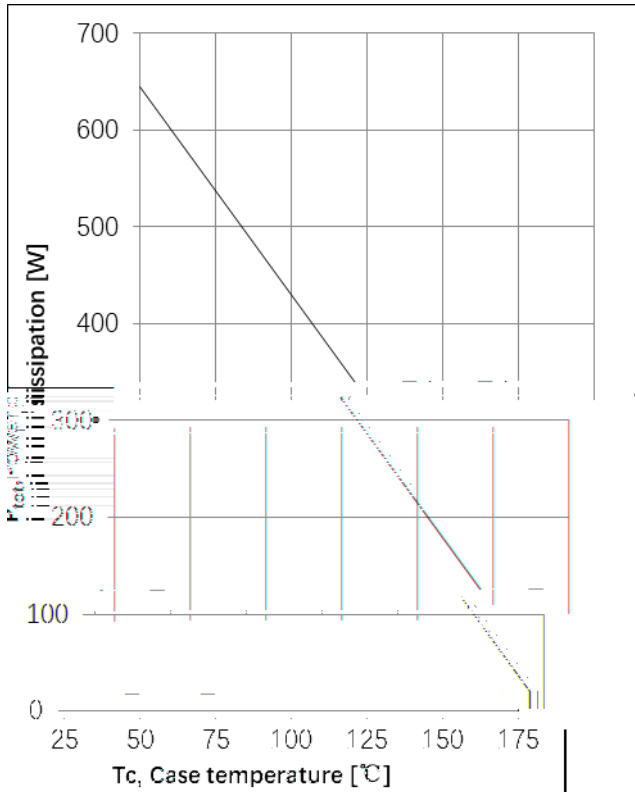


Fig1. Power dissipation as a function of case temperature ($T_J \leq 175^\circ\text{C}$)

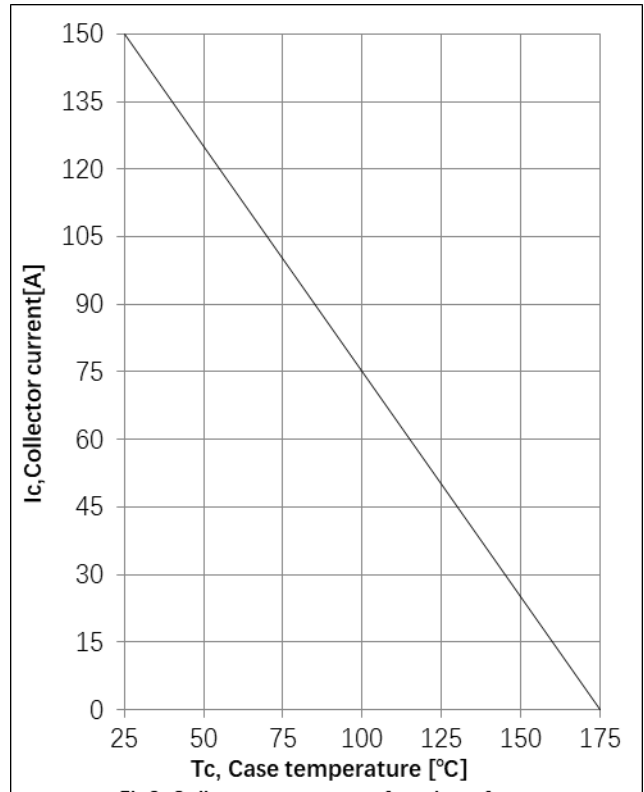
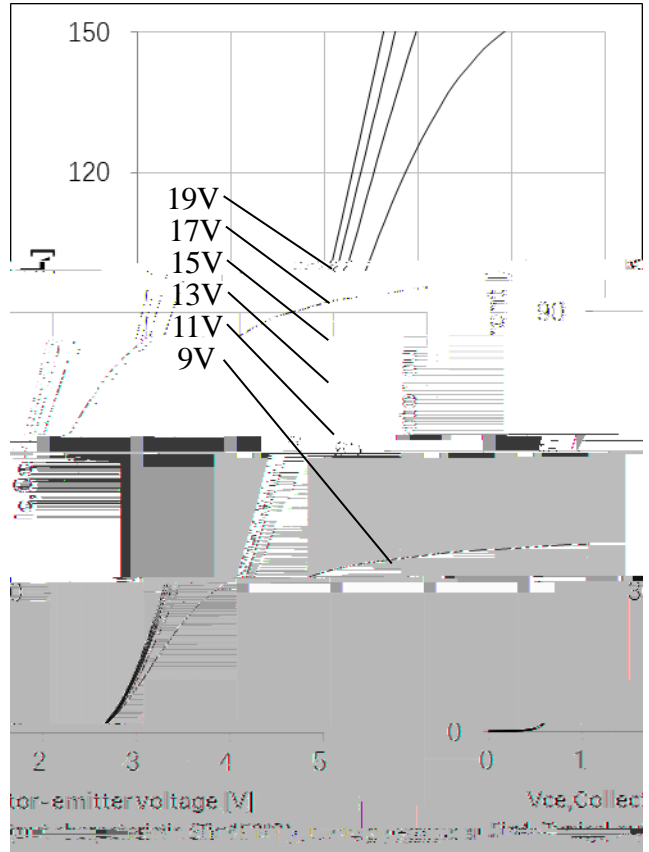
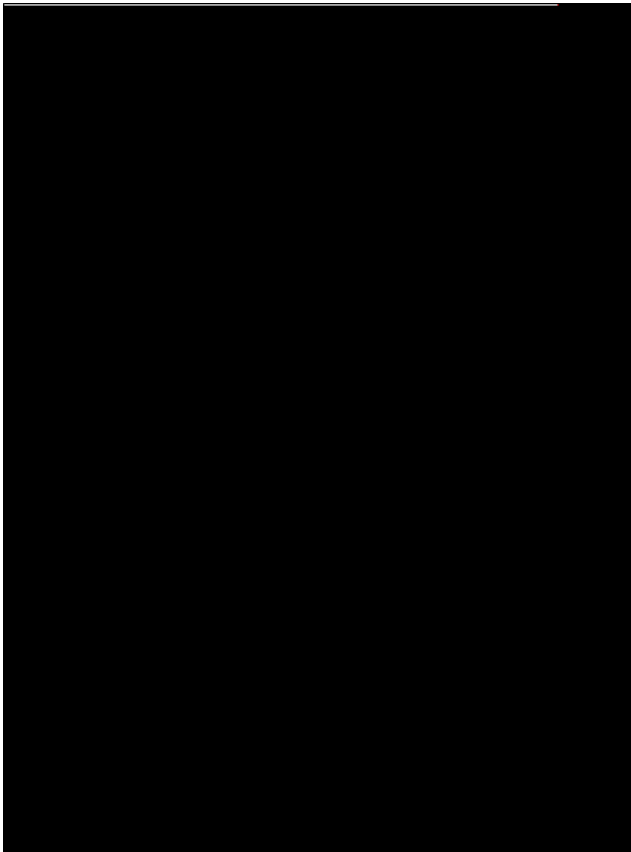
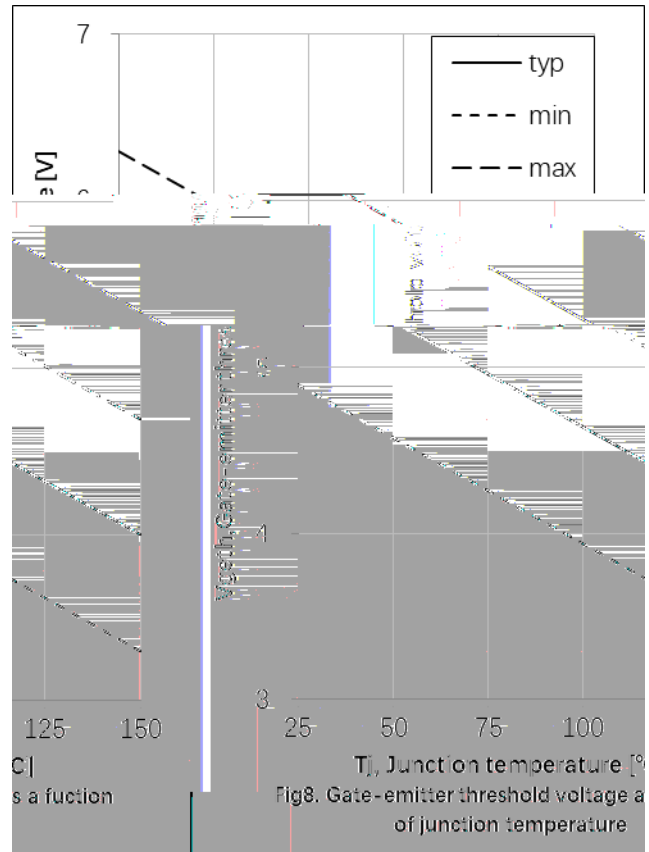
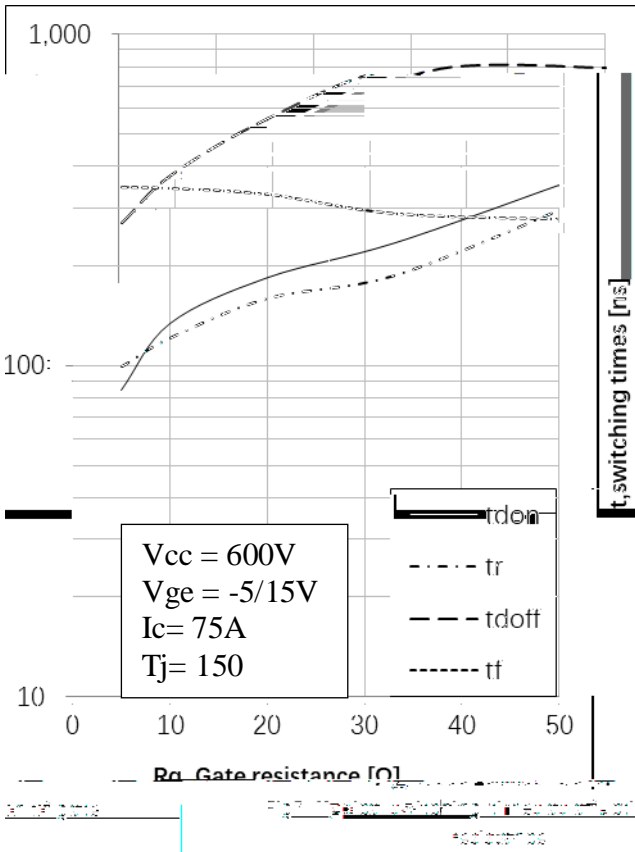
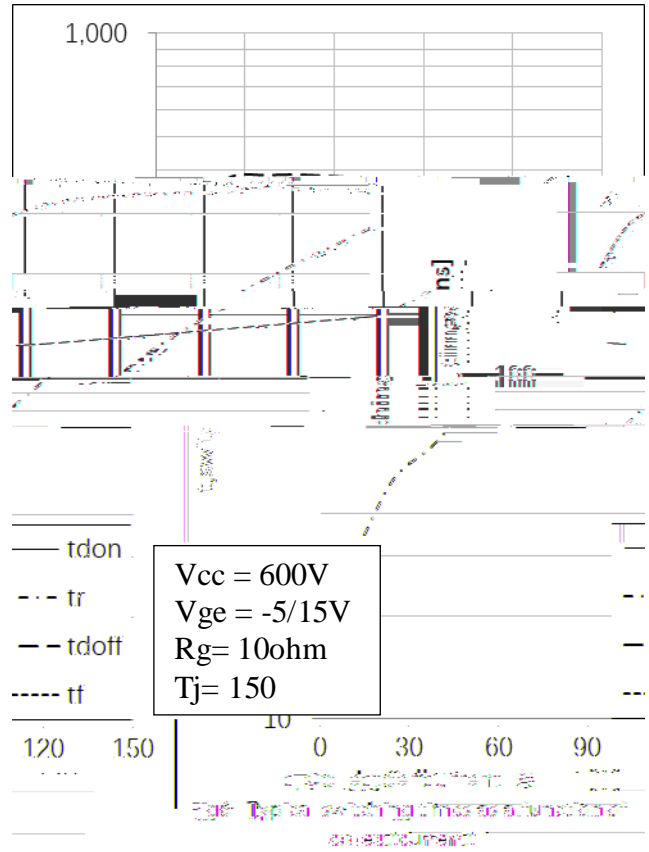
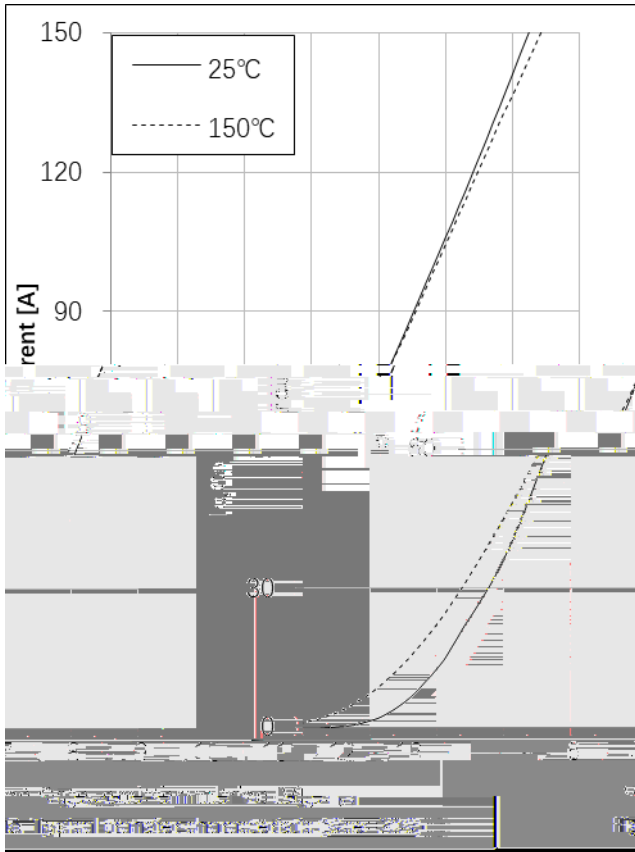


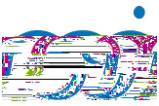
Fig2. Collector current as a function of case temperature ($V_{ge} \geq 15\text{V}$, $T_J \leq 175^\circ\text{C}$)



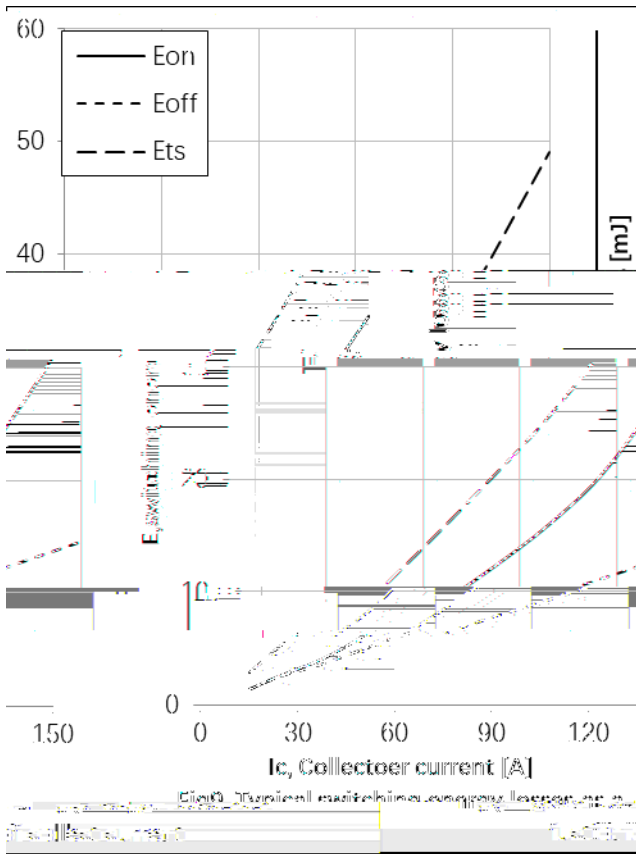


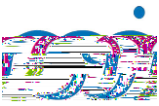
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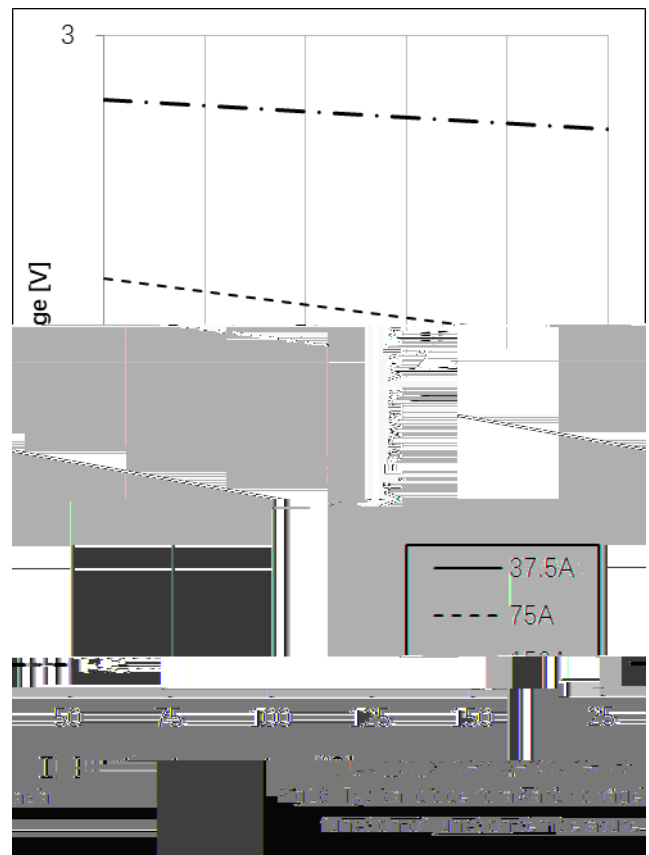
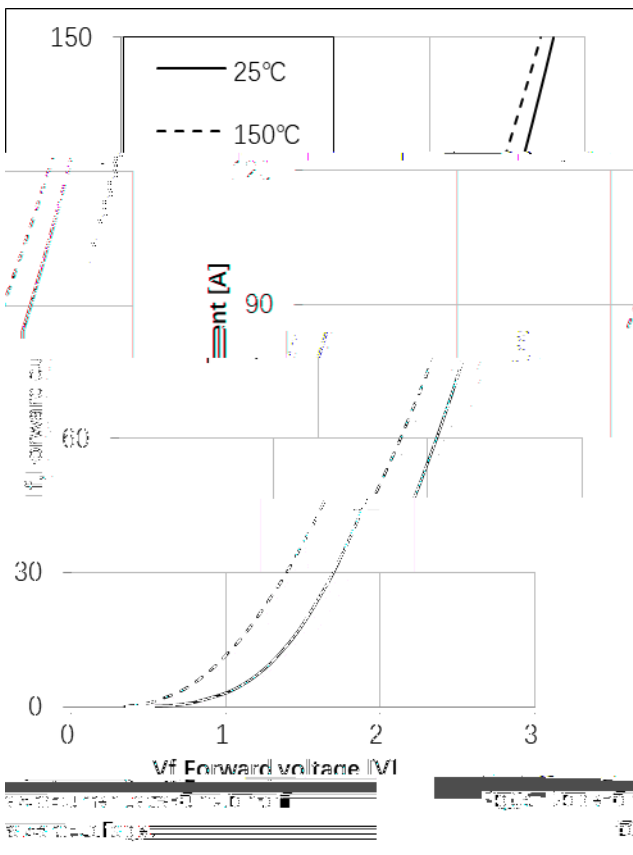
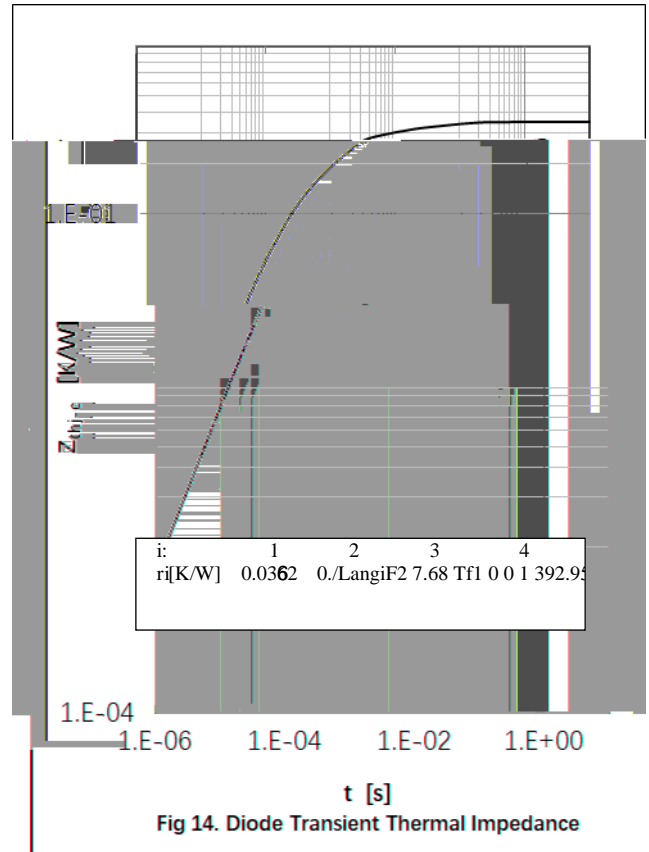
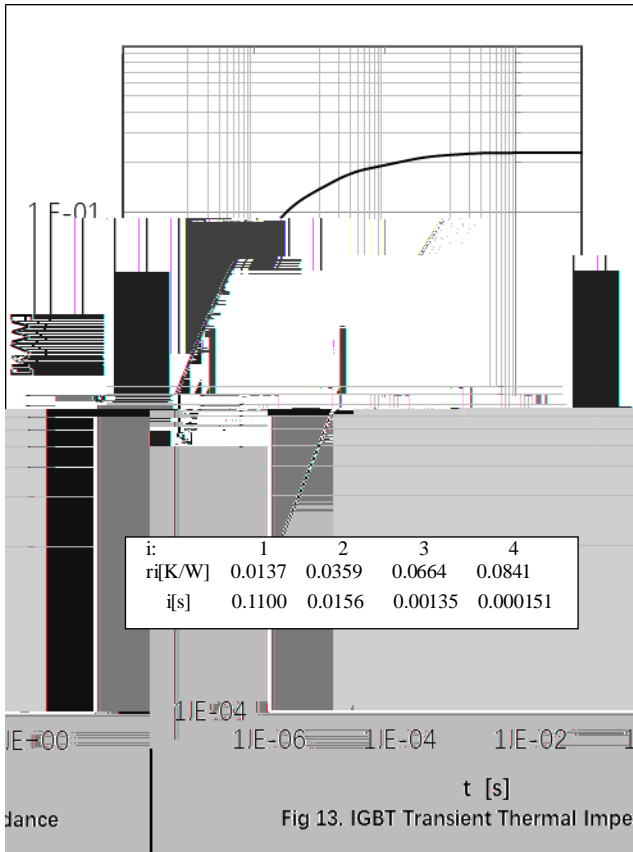


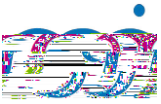
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